

Rahul Pandey

List of Publications by Year in descending order

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152
papers

2,427
citations

201674

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153
all docs

153
docs citations

153
times ranked

719
citing authors

#	ARTICLE	IF	CITATIONS
1	Device simulation of 17.3% efficient lead-free all-perovskite tandem solar cell. Solar Energy, 2020, 197, 212-221.	6.1	188
2	Interfacial Charge Analysis of Heterogeneous Gate Dielectric-Gate All Around-Tunnel FET for Improved Device Reliability. IEEE Transactions on Device and Materials Reliability, 2016, 16, 227-234.	2.0	175
3	Device simulations: Toward the design of >13% efficient PbS colloidal quantum dot solar cell. Solar Energy, 2020, 207, 893-902.	6.1	88
4	Numerical Simulation of N ⁺ Source Pocket PIN-GAA-Tunnel FET: Impact of Interface Trap Charges and Temperature. IEEE Transactions on Electron Devices, 2017, 64, 1482-1488.	3.0	84
5	Gate Drain Underlapped-PNIN-GAA-TFET for Comprehensively Upgraded Analog/RF Performance. Superlattices and Microstructures, 2017, 102, 17-26.	3.1	63
6	Numerical simulations: Toward the design of 27.6% efficient four-terminal semi-transparent perovskite/SiC passivated rear contact silicon tandem solar cell. Superlattices and Microstructures, 2016, 100, 656-666.	3.1	58
7	Optimization of high-k and gate metal workfunction for improved analog and intermodulation performance of Gate Stack (GS)-GEWE-SiNW MOSFET. Superlattices and Microstructures, 2016, 97, 630-641.	3.1	47
8	Reliability Issues of In ₂ O ₅ Sn Gate Electrode Recessed Channel MOSFET: Impact of Interface Trap Charges and Temperature. IEEE Transactions on Electron Devices, 2018, 65, 860-866.	3.0	47
9	Gate drain-overlapped-asymmetric gate dielectric-GAA-TFET: a solution for suppressed ambipolarity and enhanced ON state behavior. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	44
10	Investigation of Carrier Transport Materials for Performance Assessment of Lead-Free Perovskite Solar Cells. IEEE Transactions on Electron Devices, 2022, 69, 3217-3224.	3.0	43
11	Numerical simulations: Toward the design of 18.6% efficient and stable perovskite solar cell using reduced cerium oxide based ETL. Vacuum, 2019, 159, 173-181.	3.5	42
12	Analysis of novel transparent gate recessed channel (TGRC) MOSFET for improved analog behaviour. Microsystem Technologies, 2016, 22, 2665-2671.	2.0	41
13	Analog and RF Performance Evaluation of Junctionless Accumulation Mode (JAM) Gate Stack Gate All Around (GS-GAA) FinFET. Silicon, 2021, 13, 919-927.	3.3	41
14	Comprehensive device simulation of 23.36% efficient two-terminal perovskite-PbS CQD tandem solar cell for low-cost applications. Scientific Reports, 2021, 11, 19829.	3.3	40
15	Impact of device parameter variation on RF performance of gate electrode workfunction engineered (GEWE)-silicon nanowire (SiNW) MOSFET. Journal of Computational Electronics, 2015, 14, 798-810.	2.5	39
16	Toward the design of monolithic 23.1% efficient hysteresis and moisture free perovskite/c-Si HJ tandem solar cell: a numerical simulation study. Journal of Micromechanics and Microengineering, 2019, 29, 064001.	2.6	38
17	Investigation of parasitic capacitances of In ₂ O ₅ Sn gate electrode recessed channel MOSFET for ULSI switching applications. Microsystem Technologies, 2017, 23, 5867-5874.	2.0	37
18	Temperature Associated Reliability Issues of Heterogeneous Gate Dielectric-Gate All Around-Tunnel FET. IEEE Nanotechnology Magazine, 2018, 17, 41-48.	2.0	34

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19	Source/Gate Material-Engineered Double Gate TFET for improved RF and linearity performance: a numerical simulation. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	34
20	Investigations aimed at producing 33% efficient perovskite-silicon tandem solar cells through device simulations. RSC Advances, 2021, 11, 37366-37374.	3.6	34
21	Enhanced Charge Extraction in Metal-Perovskite-Metal Back-Contact Solar Cell Structure Through Electrostatic Doping: A Numerical Study. IEEE Transactions on Electron Devices, 2021, 68, 1757-1763.	3.0	33
22	Power gain assessment of ITO based Transparent Gate Recessed Channel (TGRC) MOSFET for RF/wireless applications. Superlattices and Microstructures, 2016, 91, 290-301.	3.1	32
23	Numerical simulation of charge transport layer free perovskite solar cell using metal work function shifted contacts. Optik, 2020, 202, 163646.	2.9	32
24	TCAD Temperature Analysis of Gate Stack Gate All Around (GS-GAA) FinFET for Improved RF and Wireless Performance. Silicon, 2021, 13, 3741-3753.	3.3	32
25	Performance evaluation of linearity and intermodulation distortion of nanoscale GaN-SOI FinFET for RFIC design. AEU - International Journal of Electronics and Communications, 2020, 115, 153052.	2.9	31
26	Mathematical modeling insight of hetero gate dielectric-dual material gate-GAA-tunnel FET for VLSI/analog applications. Microsystem Technologies, 2017, 23, 4091-4098.	2.0	29
27	Design and Simulation of a-Si:H/PbS Colloidal Quantum Dots Monolithic Tandem Solar Cell for 12% Efficiency. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000252.	1.8	29
28	MOS based pseudo-resistors exhibiting Tera Ohms of Incremental Resistance for biomedical applications: Analysis and proof of concept. The Integration VLSI Journal, 2021, 76, 25-39.	2.1	28
29	Intermodulation distortion and linearity performance assessment of 50-nm gate length L-DUMGAC MOSFET for RFIC design. Superlattices and Microstructures, 2008, 44, 143-152.	3.1	27
30	Palladium Gate All Around - Hetero Dielectric -Tunnel FET based highly sensitive Hydrogen Gas Sensor. Superlattices and Microstructures, 2016, 100, 401-408.	3.1	27
31	Technology computer aided design of 29.5% efficient perovskite/interdigitated back contact silicon heterojunction mechanically stacked tandem solar cell for energy-efficient applications. Journal of Photonics for Energy, 2017, 7, 022503.	1.3	26
32	Numerical analysis of Mg ₂ Si/Si heterojunction DG-TFET for low power/high performance applications: Impact of non-idealities. Superlattices and Microstructures, 2020, 139, 106397.	3.1	26
33	Ultralow-power dielectric-modulated nanogap-embedded sub-20-nm TGRC-MOSFET for biosensing applications. Journal of Computational Electronics, 2018, 17, 1807-1815.	2.5	25
34	Effect of structural and temperature variations on perovskite/Mg ₂ Si based monolithic tandem solar cell structure. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	25
35	Rapid detection of biomolecules in a dielectric modulated GaN MOSHEMT. Journal of Materials Science: Materials in Electronics, 2020, 31, 16609-16615.	2.2	24
36	Numerical simulation of rear contact silicon solar cell with a novel front surface design for the suppression of interface recombination and improved absorption. Current Applied Physics, 2016, 16, 1581-1587.	2.4	23

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37	Performance investigation of heterogeneous gate dielectric-gate metal engineered "gate all around-tunnel FET for RF applications. <i>Microsystem Technologies</i> , 2017, 23, 4081-4090.	2.0	23
38	Influence of gate metal engineering on small-signal and noise behaviour of silicon nanowire MOSFET for low-noise amplifiers. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	2.3	22
39	Numerical simulations of novel SiGe-based IBC-HJ solar cell for standalone and mechanically stacked tandem applications. <i>Materials Research Bulletin</i> , 2017, 93, 282-289.	5.2	22
40	Design and optimization of 26.3% efficient perovskite/FeSi ₂ monolithic tandem solar cell. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 15218-15224.	2.2	22
41	Performance Analysis for SnS- and Sn ₂ S ₃ -Based Back Surface Field CZTSSe Solar Cell: A Simulation Study. <i>Journal of Electronic Materials</i> , 2021, 50, 6318-6328.	2.2	21
42	Rear contact SiGe solar cell with SiC passivated front surface for >90-percent external quantum efficiency and improved power conversion efficiency. <i>Solar Energy</i> , 2016, 135, 242-252.	6.1	20
43	Impact of metal silicide source electrode on polarity gate induced source in junctionless TFET. <i>Applied Physics A: Materials Science and Processing</i> , 2019, 125, 1.	2.3	20
44	Numerical simulation and proof of concept for performance assessment of cesium based lead-free wide-bandgap halide solar cells. <i>Optical Materials</i> , 2021, 111, 110644.	3.6	20
45	Radiation Analysis of N-Channel TGRC-MOSFET: An X-Ray Dosimeter. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 5014-5020.	3.0	19
46	Sub-30nm In ₂ O ₅ Sn gate electrode recessed channel MOSFET: A biosensor for early stage diagnostics. <i>Vacuum</i> , 2019, 164, 46-52.	3.5	19
47	Novel back-contact back-junction SiGe (BC-BJ SiGe) solar cell for improved power conversion efficiency. <i>Microsystem Technologies</i> , 2016, 22, 2673-2680.	2.0	18
48	A 1.1 μ W biopotential amplifier based on bulk-driven quasi-floating gate technique with extremely low-value of offset voltage. <i>Analog Integrated Circuits and Signal Processing</i> , 2020, 103, 303-313.	1.4	18
49	Numerical Study of JAM-GS-GAA FinFET: A Fin Aspect Ratio Optimization for Upgraded Analog and Intermodulation Distortion Performance. <i>Silicon</i> , 2022, 14, 309-321.	3.3	16
50	RF Analysis of Double-Gate Junctionless Tunnel FET for Wireless Communication Systems: A Non-quasi Static Approach. <i>Journal of Electronic Materials</i> , 2021, 50, 138-154.	2.2	15
51	A novel source material engineered double gate tunnel field effect transistor for radio frequency integrated circuit applications. <i>Semiconductor Science and Technology</i> , 2020, 35, 105013.	2.0	14
52	Numerical simulations of 22% efficient all-perovskite tandem solar cell utilizing lead-free and low lead content halide perovskites. <i>Journal of Micromechanics and Microengineering</i> , 2022, 32, 014004.	2.6	14
53	Gate Drain Underlapping: A Performance Enhancer For HD-GAA-TFET. <i>Materials Today: Proceedings</i> , 2018, 5, 17453-17463.	1.8	13
54	Comprehensive Study on the Recent Development of PERC Solar Cell. , 2020, , .		13

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55	The Effect of Gate Stack and High-Å, Spacer on Device Performance of a Junctionless GAA FinFET. , 2020, , .		12
56	Gate Oxide Variability Analysis of a Novel 3 nm Truncated Finâ€“FinFET for High Circuitry Performance. Silicon, 2021, 13, 3249-3256.	3.3	12
57	Design and Investigation of Recessed-T-Gate Double Channel HEMT with InGaN Back Barrier for Enhanced Performance. Arabian Journal for Science and Engineering, 2022, 47, 1109-1116.	3.0	12
58	22.8% efficient ion implanted PERC solar cell with a roadmap to achieve 23.5% efficiency: A process and device simulation study. Optical Materials, 2022, 128, 112399.	3.6	12
59	Sensitivity Analysis of Biomolecule Nanocavity Immobilization in a Dielectric Modulated Triple-Hybrid Metal Gate-All-Around Junctionless NWFET Biosensor for Detecting Various Diseases. Journal of Electronic Materials, 2022, 51, 2236-2247.	2.2	11
60	Oxide bound impact on hot-carrier degradation for gate electrode workfunction engineered (GEWE) silicon nanowire MOSFET. Microsystem Technologies, 2016, 22, 2655-2664.	2.0	10
61	Conducting Polymer Based Gas Sensor Using PNIN- Gate All Around - Tunnel FET. Silicon, 2020, 12, 2947-2955.	3.3	10
62	TCAD investigation of ferroelectric based substrate MOSFET for digital application. Silicon, 2022, 14, 5075-5084.	3.3	10
63	Role of Junctionless Mode in Improving the Photosensitivity of Sub-10 nm Carbon Nanotube/Nanoribbon Field-Effect Phototransistors: Quantum Simulation, Performance Assessment, and Comparison. Nanomaterials, 2022, 12, 1639.	4.1	10
64	Numerical simulation and parametric assessment of GaN buffered trench gate MOSFET for low power applications. IET Circuits, Devices and Systems, 2020, 14, 915-922.	1.4	9
65	Microstates-based resting frontal alpha asymmetry approach for understanding affect and approach/withdrawal behavior. Scientific Reports, 2020, 10, 4228.	3.3	9
66	Influence of SnS and Sn₂S₃ based BSF layers on the performance of CZTSSe solar cell. , 2020, , .		9
67	Performance Analysis of Drain Pocket Hetero Gate Dielectric DG-TFET: Solution for Ambipolar Conduction and Enhanced Drive Current. Silicon, 2022, 14, 8097-8107.	3.3	9
68	Temperature associated reliability issues of heterogeneous gate dielectric-gate all around-tunnel FET. , 2016, , .		8
69	Designing of CZTSSe Based SnS Thin Film Solar Cell for Improved Conversion Efficiency: A Simulation Study with SCAPS. , 2019, , .		8
70	Comprehensive device simulation of 16.9% efficient two-terminal PbSâ€“PbS CQD tandem solar cell. Optical Materials, 2021, 122, 111677.	3.6	8
71	Chemical modulation of conducting polymer gate electrode work function based double gate Mg2Si TFET for gas sensing applications. Journal of Materials Science: Materials in Electronics, 2022, 33, 23927-23936.	2.2	8
72	Ultrascaled 10Ånm Taâ€“gate Eâ€“mode <sc>InAlN</sc> / <sc>AlN HEMT</sc> with polarized doped buffer for high power microwave applications. International Journal of RF and Microwave Computer-Aided Engineering, 2022, 32, .	1.2	8

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73	Analog/RF Performance and Effect of Temperature on Ferroelectric Layer Improved FET device with Spacer. Silicon, 2022, 14, 12269-12280.	3.3	8
74	Design and parametric optimization of ion-implanted PERC solar cells to achieve 22.8% efficiency: a process and device simulation study. Sustainable Energy and Fuels, 2022, 6, 3249-3262.	4.9	8
75	Sub-10 nm High-k Dielectric SOI-FinFET for HighPerformance Low Power Applications. , 2020, , .		7
76	Numerical simulations of a novel CH ₃ NH ₃ PbI ₃ based double-gate dopingless tunnel FET. Semiconductor Science and Technology, 0, , .	2.0	7
77	Magnesium Silicide Source Double Palladium Metal Gate TFET for Highly Sensitive Hydrogen Gas Sensor. , 2021, , .		7
78	Design and simulations of 24.7% efficient silicide on oxide-based electrostatically doped (SILO-ED) carrier selective contact PERC solar cell. , 2022, , 207200.		7
79	Process and device simulations aimed at improving the emitter region performance of silicon PERC solar cells. Journal of Micromechanics and Microengineering, 2022, 32, 025001.	2.6	7
80	Implications of transport models on the analog performance of Gate Electrode Workfunction Engineered (GEWE) Silicon Nanowire MOSFET. , 2014, , .		6
81	Gate metal engineered heterojunction DG-TFETs for superior analog performance and enhanced device reliability. , 2017, , .		6
82	Rear contact silicon solar cells with a-SiC _x H based front surface passivation for near-ultraviolet radiation stability. Superlattices and Microstructures, 2018, 122, 111-123.	3.1	6
83	Impact of Graded Back-Barrier on Linearity of Recessed Gate InAlN/GaN HEMT. , 2020, , .		6
84	Band gap and gate metal engineering of novel hetero-material InAs/GaAs-based JLTFTET for improved wireless applications. Journal of Materials Science: Materials in Electronics, 2021, 32, 3155-3166.	2.2	6
85	Fin Aspect Ratio Optimization of Novel Junctionless Gate Stack Gate All Around (GS-GAA) FinFET for Analog/RF Applications. Lecture Notes in Electrical Engineering, 2021, , 59-67.	0.4	6
86	Assessment of WSe ₂ based BSF layer on CZTSSe solar cell using SCAPS-1D. , 2021, , .		6
87	Numerical simulation of analog metrics and parasitic capacitances of GaAs GS-GAA FinFET for ULSI switching applications. European Physical Journal Plus, 2022, 137, 1.	2.6	6
88	A Numerical Study of Analog Parameter of Negative Capacitance Field Effect Transistor with Spacer. , 2021, , .		6
89	Detection of biomolecules in dielectric modulated double metal below ferroelectric layer FET with improved sensitivity. Journal of Materials Science: Materials in Electronics, 2022, 33, 13558-13567.	2.2	6
90	Silicide on Oxide Based Carrier Selective Front Contact for 24% Efficient PERC Solar Cell. , 2022, , .		6

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91	PNIN-GAA-tunnel FET with palladium catalytic metal gate as a highly sensitive hydrogen gas sensor. , 2017, , .		5
92	Design Considerations and Capacitance Dependent Parametric Assessment of Gate Metal Engineered SiNW MOSFET for ULSI Switching Applications. Silicon, 2020, 12, 1501-1510.	3.3	5
93	Optimization of Mixed Sn and Pb Perovskite Solar Cell in Terms of Transport Layers and Absorber Layer Thickness Variation. , 2021, , .		5
94	Process voltage temperature analysis of MOS based balanced pseudo-resistors for biomedical analog circuit applications. Circuit World, 2021, , .	0.9	5
95	GaN Silicon-on-Insulator (SOI) N-Channel FinFET for High-Performance Low Power Applications. , 2019, , .		5
96	Effect of dielectric engineering on analog and linearity performance of gate electrode workfunction engineered (GEWE) silicon nanowire MOSFET. , 2015, , .		4
97	Novel 4-terminal perovskite/SiC-based rear contact silicon tandem solar cell with 27.6 % PCE. , 2016, , .		4
98	Source material assessment of heterojunction DG-TFET for improved analog performance. , 2017, , .		4
99	Small-signal modeling of In ₂ O ₅ Sn based transparent gate recessed channel MOSFET for microwave/RF applications. , 2017, , .		4
100	Analysis of Varied Dielectrics as Surface Passivation on AlGaIn/GaN HEMT for Analog Applications. , 2018, , .		4
101	Silicide Electrode based Electrostatically Doped Back Surface Field in PERC Solar Cell. , 2021, , .		4
102	Impact of Phosphorus Ion Implantation Dose on the Performance of PERC Solar Cell. , 2021, , .		4
103	Design and Optimization of Low Lead Content- Based Mixed Sn and Pb Perovskite Solar Cell for 19.46% Efficiency. , 2021, , .		4
104	Effect of temperature on analog performance of Mg ₂ Si source heterojunction double gate tunnel field effect transistor. Materials Today: Proceedings, 2020, 28, 1520-1524.	1.8	4
105	Front Surface Passivation Scheme for Back-Contact Back-Junction (BC-BJ) Silicon Solar Cell. Advanced Science Letters, 2016, 22, 815-820.	0.2	4
106	Optimization of inversion mode and junctionless nanowire MOSFET for improved sensitivity to process induced variability. Applied Nanoscience (Switzerland), 2022, 12, 2161-2168.	3.1	4
107	Novel SiC encapsulated coaxial silicon nanowire solar cell for optimal photovoltaic performance. , 2015, , .		3
108	Rear contact solar cell with ZrO ₂ nano structured front surface for efficient light trapping and enhanced surface passivation. , 2015, , .		3

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109	Linearity performance of Gate Metal Engineered (GME) Omega Gate-Silicon Nanowire MOSFET: A TCAD study. , 2016, , .		3
110	Electrical Characteristics Assessment of Gate Metal and Source Pocket Engineered DG-TFET for Low Power Analog Applications. , 2018, , .		3
111	Numerical Simulation of CeO _x ETL based Perovskite Solar Cell:- An Optimization Study for High Efficiency and Stability. , 2018, , .		3
112	Performance Analysis of Heterojunction DMDG-TFET with Different Source Materials for Analog Application. , 2018, , .		3
113	Heterojunction DG-TFET-Analysis of Different Source Material for Improved Intermodulation. , 2018, , .		3
114	GaAs Junctionless FinFET Using High-k Dielectric for High-Performance Applications. , 2018, , .		3
115	Investigation of electrical/analog performance and reliability of gate metal and source pocket engineered DG-TFET. Microsystem Technologies, 2020, , 1.	2.0	3
116	Reliability of Sub-20Ånm Black Phosphorus Trench (BP-T) MOSFET in High-Temperature Harsh Environment. Silicon, 2021, 13, 1277-1283.	3.3	3
117	A methodical survey on present state of art for electrostatically-doped tunnel FETs and its future prospects. Materials Today: Proceedings, 2021, 45, 5381-5386.	1.8	3
118	Reliability analysis of cost-efficient CH ₃ NH ₃ PbI ₃ based dopingless tunnel FET. Semiconductor Science and Technology, 2022, 37, 015011.	2.0	3
119	RF, linearity and intermodulation distortion analysis with small-signal parameters extraction of tunable bandgap arsenide/antimonide tunneling interfaced JLTfET. Microsystem Technologies, 2022, 28, 2659-2667.	2.0	3
120	Source Material-Engineered Charge Plasma based Double Gate TFET for Analog/RF Applications. , 2021, , .		3
121	Impact of Channel Doping and Gate Length on Small Signal Behaviour of Gate Electrode Workfunction Engineered Silicon Nanowire MOSFET at THz Frequency. , 2014, , .		2
122	Parametric Variation of ZnSe/TiO ₂ Electron Transport Layer Based Perovskite Solar Cell: A Simulation Study and Optimization. , 2018, , .		2
123	Design and Simulation of Novel Perovskite/Mg ₂ Si Based Monolithic Tandem Solar Cell With 25.5% Conversion Efficiency. , 2019, , .		2
124	Carbon Nanotube Recessed Channel (CNT-RC) MOSFET for High Linearity/UlSI Applications. , 2019, , .		2
125	TCAD Analysis and Modelling of Gate-Stack Gate All Around Junctionless Silicon NWFET Based Bio-Sensor for Biomedical Application. , 2020, , .		2
126	Thickness Optimisation and Defect Analysis of Wide Bandgap PbS-CQD Solar Cell by SCAPS-1D Simulations. , 2021, , .		2

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127	Impact of interfacial charges on analog and RF performance of Mg ₂ Si source heterojunction double-gate tunnel field effect transistor. Journal of Materials Science: Materials in Electronics, 2021, 32, 23863-23879.	2.2	2
128	Performance Evaluation of Lead-free Perovskite Solar Cell with Different Hole/Electron Transport Materials. , 2020, , .		2
129	Quantum analysis based extraction of frequency dependent intrinsic and extrinsic parameters for GEWE-SiNW MOSFET. Journal of Computational Electronics, 2017, 16, 61-73.	2.5	1
130	Reliability of high-k gate stack on transparent gate recessed channel (TGRC) MOSFET. , 2017, , .		1
131	A moisture stable, hysteresis-free semi-transparent perovskite solar cell with single wall carbon nanotubes. , 2018, , .		1
132	Investigation of Different Gate Materials for Improved Device Performance in RC MOSFET. , 2018, , .		1
133	Effect of Temperature on GaAs Junctionless FinFET Using High- ϵ^p Dielectric. , 2019, , .		1
134	Current Reference Circuit Operable at Low Voltages Using Composite MOS Triode Resistor. , 2020, , .		1
135	Analysis of a Novel Nanoscale Vacuum Channel TF-FinFET. Silicon, 2021, 13, 3257-3269.	3.3	1
136	Technology Computer Aided Design of a Novel Fully Gate Covered Channel Junctionless SOI FinFET for high performance analog application. , 2021, , .		1
137	Numerical Simulation and Optimisation of Wide Bandgap (1.45eV) PbS-CQD Solar Cell for 14% Conversion Efficiency. , 2021, , .		1
138	Device Simulation of Poly (3-Hexylthiophene) HTL Based Single and Double Halide Perovskite Solar Cells. , 2020, , .		1
139	Built-in Reliability Investigation of Gate-Drain Underlapped PNIN-GAA-TFET for Improved Linearity and Reduced Intermodulation Distortion. Lecture Notes in Electrical Engineering, 2020, , 205-213.	0.4	1
140	Numerical simulations of PbS colloidal quantum dots solar cell with ZnO: PEIE-based electron transport layer. Indian Journal of Physics, 2022, 96, 4203-4208.	1.8	1
141	Linearity Performance of Double Metal Negative Capacitance Field-Effect Transistors: A Numerical Study. , 2022, , .		1
142	Interdigitated back contact silicon solar cell with perovskite layer for front surface passivation and ultraviolet radiation stability. , 2017, , .		0
143	Temperature Reliability of Junctionless Twin Gate Recessed Channel (JL-TGRC) MOSFET with Different Gate Material for Low Power Digital-Logic Applications. , 2018, , .		0
144	Capacitive Analysis of Hetero Material Gate PNIN-DG-TFET Over Diverge Temperature Range for Superior RF/Microwave Performance. , 2018, , .		0

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145	Non-Quasi-Static Small-Signal Modeling of TGRC MOSFET in Parameter Perspective for RF/Microwave Applications. , 2019, , .		0
146	Numerical Simulations to Understand the Role of DIO Additive in PTB7:PC71BM Solar Cell. , 2019, , .		0
147	Challenges faced in running "Train the Trainers"™ program by industry professionals and possible solutions. Procedia Computer Science, 2020, 172, 427-432.	2.0	0
148	A Low-Power gm-C Filter for Neural Signal Conditioning. , 2020, , .		0
149	Impact of Ferroelectric Oxide Layer on Palladium Silicide Source Electrode based Double-Gate Junctionless TFET. , 2021, , .		0
150	Analog Analysis of Novel Ferroelectric-Dual Material Oxide Stack-Double Gate FET. , 2021, , .		0
151	Mg ₂ Si/Si heterojunction dopingless TFET with reduced random dopant fluctuations for low power applications. Journal of Materials Science: Materials in Electronics, 2022, 33, 6816-6828.	2.2	0
152	RF Analysis of a Fully Gate Covered Junctionless FinFET for Improved Performance. , 2022, , .		0